



THE PENDING CLAIMS:

1. (Original) A sprayed coating formed by plasma spraying inside a semiconductor processing device, the coating comprising:

· a metal oxide composed of oxygen and a metal, or a semiconductor oxide composed of oxygen and a semiconductor;

wherein a composition ratio of the oxygen with respect to the metal or the semiconductor is not less than 80% of a composition ratio of the stoichiometric composition.

2. (Original) The sprayed coating according to claim 1, wherein the metal or the semiconductor comprises at least one of an alkaline-earth metal, a rare-earth metal, Al, Ta, and Si.

3. (Original) The sprayed coating according to claim 1, wherein the metal oxide is aluminum oxide and a percentage of actual composition ratio to stoichiometric composition ratio is not less than 85%.

4. (Original) The sprayed coating according to claim 1, wherein the metal oxide is magnesium oxide and a percentage of actual composition ratio to stoichiometric composition ratio is not less than 81%.

5. (Original) The sprayed coating according to claim 1, wherein the metal oxide is yttrium oxide and a percentage of actual composition ratio to stoichiometric composition ratio is not less than 85%.

6. (Withdrawn) A production method for a sprayed coating, comprising a step of forming a coating by plasma spraying inside a semiconductor processing device, wherein a plasma operating gas is oxygen gas or a gas including oxygen.

7. (Withdrawn) The production method for a sprayed coating according to claim 6, wherein the atmosphere in which plasma spraying is conducted is air.